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In the Claims:

The claims are to be amended as follows:

1-9. (Cancelled).

10. (Currently Amended) A space transformer comprising:

a silicon medium having a land grid array side and a semiconductor side opposite the land grid array side; and

a predetermined contact pattern comprising electrically conductive material disposed in an inner region of the ~~substrate~~ silicon medium and defining electrical contact zones ~~located to provide~~ providing double-sided electrical contacts for the space transformer, the contacts comprising:

land grid array side contacts disposed on the land grid array side of the silicon medium and having their largest dimension and their pitch in the order of mils to define a macro-pitch scale; and

semiconductor side contacts disposed on the semiconductor side of the silicon medium and having their largest dimension and their pitch in the order of microns to define a micro-pitch scale, the electrical contact zones being disposed to convert a macro-pitch scale of the land grid array side contacts to the micro-pitch scale of the semiconductor side contacts, ~~said land grid array side contacts having dimensions and spacing larger than said semiconductor side contacts.~~

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11. (Original) The space transformer according to claim 10, wherein the silicon medium comprises a first silicon layer and a second silicon layer, the contact pattern being disposed between the first silicon layer and the second silicon layer.

12. (Previously Presented) The space transformer according to claim 11, wherein the second silicon layer defines at least one via therein, at least some of the electrically conductive material being located in the at least one via.

13. (Original) The space transformer according to claim 11, further comprising an adhesion promoter disposed between the electrically conductive material and the first silicon layer.

14. (Currently Amended) A space transformer comprising:

a silicon medium having a land grid array side and a semiconductor side opposite the land grid array side and further comprising a first silicon layer defining a plurality of vias therein and a second silicon layer disposed on the first silicon layer;

a predetermined contact pattern comprising copper on the first silicon layer and being disposed in an inner region located between the first silicon layer and the second silicon layer, at least some of the copper being disposed in the plurality of vias for defining ~~thermal~~ electrical contact zones ~~in the plurality of vias to provide providing~~ double-sided electrical contacts for the space transformer; ~~and a second silicon layer disposed on the contact pattern, the contact pattern being disposed in an inner region~~

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~~located between the first silicon layer and the second silicon layer,~~ the contacts comprising:

land grid array side contacts disposed on the land grid array side of the silicon medium and having their largest dimension and their pitch in the order of mils to define a macro-pitch scale; and

semiconductor side contacts disposed on the semiconductor side of the silicon medium and having their largest dimension and their pitch in the order of microns to define a micro-pitch scale, the electrical contact zones being disposed to convert a macro-pitch scale of the land grid array side contacts to the micro-pitch scale of the semiconductor side contacts, ~~said land grid array side contacts having dimensions and spacing larger than said semiconductor side contacts.~~

15. (Original) The space transformer according to claim 14, further comprising a layer of adhesion promoter disposed between the electrically conductive material and the first silicon layer.

16-17. (Cancelled)